

### ***REMARKS***

Claims 1, 5-9, 11, 14-18, and 21-31 are pending in the present application. By this reply, claims 28-31 have been added. Claims 1, 11, 18, and 28-31 are independent claims.

### **DRAWING OBJECTION**

The drawings have been objected to because they fail to show the first active region having a ring configuration as recited in claim 22. To overcome this drawing objection, claim 22 has been amended to clarify that the third active region has a ring configuration which is supported by the original disclosure, e.g., page 10, lines 8-9 of the specification and Fig. 3. This corrects the typographical error in claim 22. Accordingly, the drawing objection should be withdrawn.

### **35 U.S.C. § 112, SECOND PARAGRAPH, REJECTION**

Claims 7 and 22 have been rejection under 35 U.S.C. § 112, second paragraph, as being indefinite. To overcome this rejection, claims 7 and 22 have been amended to clarify the invention. Accordingly, reconsideration and withdrawal of the rejection is respectfully requested.

**ALLOWABLE SUBJECT MATTER**

Claims 6, 14, 24 and 27 have been objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Accordingly, claims 6, 14, 24 and 27 have been rewritten in independent form and are presented herewith as new claims 28-31, respectively. Thus, indication of allowance of claims 28-31 is proper and respectfully requested.

**35 U.S.C. § 102(e) REJECTION**

Claims 1, 8, 9, 11, 15-18, 21-23 and 26 have been rejected under 35 U.S.C. § 102(e) as being anticipated by *Pan* (U.S. Patent No. 6,259,139). This rejection, insofar as it pertains to the presently pending claims, is respectfully traversed.

Regarding independent claims 1 and 11, the Examiner equates *Pan*'s drain 33 shown in the middle region of Fig. 3B to Applicants' second active region. Regarding independent claim 18, the Examiner equates *Pan*'s source 34 shown in the middle region of Fig. 3B to Applicants' second active region. However, Applicants' embodied second active region, e.g., the region 201 shown in Fig. 3, is without a gate, a drain or a source and thus cannot be equated to *Pan*'s drain 33 or source 34 of Fig. 3B. To emphasize this distinction, independent claims 1, 11 and 18 have been amended.

Thus, *Pan* does not teach or suggest, *inter alia*:

the second active region includes an n+ junction connected to Vcc reference voltage or a p+ junction connected to ground Vss, and is without a gate, a source and a drain

as recited in independent claim 1;

second active region includes an n+ junction connected to Vcc reference voltage, and is without a gate, a source and a drain

as recited in independent claim 11; and

second active region includes a p+ junction connected to ground Vss, and is without a gate, a source and a drain

as recited in independent claims 18.

Accordingly, independent claims 1, 11 and 18 and their dependent claims (due to their dependency) are patentable over *Pan*, and reconsideration and withdrawal of the rejection is respectfully requested.

### **35 U.S.C. § 103 REJECTION**

Claim 5 has been rejected under 35 U.S.C. § 103(a) as being unpatentable over *Pan* in view of *Lien et al.* (U.S. Patent No. 5,847,429). This rejection, insofar as it pertains to the presently pending claims, is respectfully traversed.

As discussed above, *Pan* does not teach or suggest, *inter alia*:

the second active region includes an n+ junction connected to Vcc reference voltage or a p+ junction connected to ground Vss, and is without a gate, a source and a drain

as recited in independent claim 1 from which claim 5 depends. *Lien et al.* does not overcome this deficiency of *Pan* since *Lien et al.* discloses a plurality of sources, drains and gates connected to each other without any second active region formed therebetween.

Thus, claim 5 is patentable over the applied references, and reconsideration and withdrawal of the rejection is respectfully requested.

### **CONCLUSION**

For the foregoing reasons and in view of the above clarifying amendments, Applicants respectfully request the Examiner to reconsider and withdraw all of the objections and rejections of record, and earnestly solicit an early issuance of a Notice of Allowance.

The Examiner is respectfully requested to enter this Amendment After Final, in that it raises no new issues but merely places the claims in a form more clearly patentable over the references of record. In the alternative, the Examiner is respectfully requested to enter this Amendment After Final in that it reduces the issues for appeal.

Should there be any outstanding matters which need to be resolved in the present application, the Examiner is respectfully requested to contact Esther H. Chong (Registration No. 40,953) at the telephone number of the undersigned below, to conduct an interview in an effort to expedite prosecution in connection with the present application.

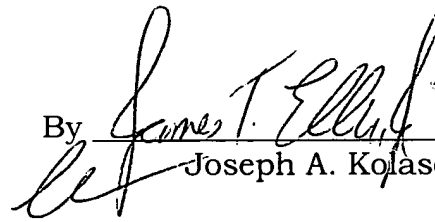
Attached hereto is a marked-up version of the changes made to the application by this Amendment.

Applicant(s) respectfully petitions under the provisions of 37 C.F.R. § 1.136(a) and 1.17 for a one month extension of time in which to respond to the Examiner's Office Action. The Extension of Time Fee in the amount of \$110.00 is attached hereto.

If necessary, the Commissioner is hereby authorized in this, concurrent, and further replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17; particularly, extension of time fees.

Respectfully submitted,

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Enclosure: Version with Markings to Show Changes Made

**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

*In the Claims*

The claims have been amended as follows:

1. (Twice Amended) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed on the semiconductor substrate;

a plurality of gates formed in each of the first active regions;

at least one second active region of a predetermined conductive type formed additionally between the first active regions, wherein the second active region includes an n<sup>+</sup> junction connected to V<sub>cc</sub> reference voltage or a p<sup>+</sup> junction connected to ground V<sub>ss</sub>, and is without a gate, a source and a drain;  
and

a third active region surrounding the first and second active regions and being of conductivity type different from that of the first active regions.

7. (Amended) The device of claim 1, further comprising:

a plurality of source regions each formed between a [the] pair of gates in each of the first active regions.

11. (Twice Amended) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed separately on the semiconductor substrate;

a plurality of gates formed in each of the first active regions; and

at least one predetermined conductive type second active region formed between two of the first active regions, wherein the predetermined conductive type second active region includes [is] an n<sup>+</sup> junction connected to V<sub>cc</sub> reference voltage, and is without a gate, a source and a drain.

18. (Twice Amended) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed separately on the semiconductor substrate;

a plurality of gates formed in each of the first active regions;

at least one second active region of a predetermined conductive type, formed between the first active regions, wherein the predetermined conductive type second active region includes a p<sup>+</sup> junction connected to ground V<sub>ss</sub>, and is without a gate, a source and a drain; and

a third active region surrounding the first and second active regions and

being of conductivity type different from that of the first active regions.

22. (Amended) The device of claim 21, wherein the third [first] active region has a ring configuration.

Claims 28-31 have been added.